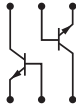


CMLT5551

**SURFACE MOUNT SILICON
DUAL, HIGH VOLTAGE
NPN TRANSISTOR**



SOT-563 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLT5551 consists of two individual, isolated NPN silicon transistors manufactured by the epitaxial planar process and epoxy molded in an SOT-563 surface mount package. This device has been designed for high voltage amplifier applications.

MARKING CODE: 5C5

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_{CBO} 180
 V_{CEO} 160
 V_{EBO} 6.0
 I_C 600
 P_D 350
 T_J, T_{stg} -65 to +150
 Θ_{JA} 357

UNITS

V
V
V
mA
mW
 $^{\circ}\text{C}$
 $^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS PER TRANSISTOR: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

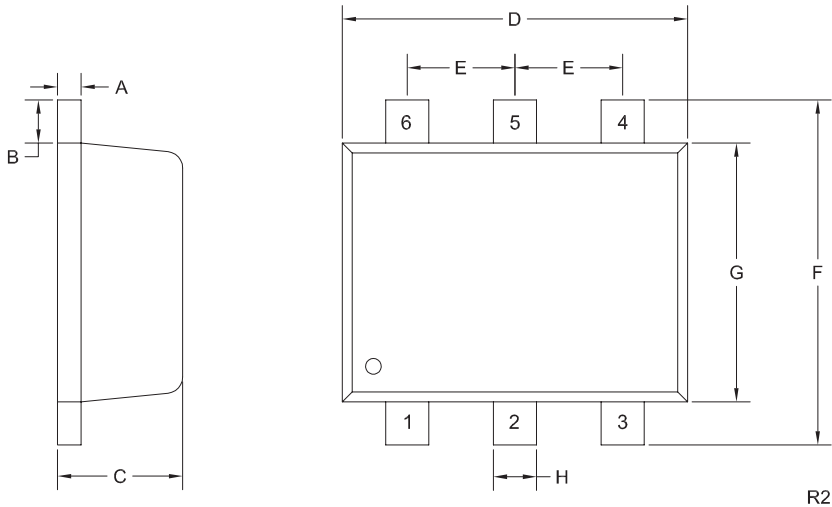
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=120\text{V}$		50	nA
I_{CBO}	$V_{CB}=120\text{V}, T_A=100^{\circ}\text{C}$		50	μA
BV_{CBO}	$I_C=100\mu\text{A}$	180		V
BV_{CEO}	$I_C=1.0\text{mA}$	160		V
BV_{EBO}	$I_E=10\mu\text{A}$	6.0		V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		0.15	V
$V_{CE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		0.20	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		1.00	V
$V_{BE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		1.00	V
h_{FE}	$V_{CE}=5.0\text{V}, I_C=1.0\text{mA}$	80		
h_{FE}	$V_{CE}=5.0\text{V}, I_C=10\text{mA}$	80	250	
h_{FE}	$V_{CE}=5.0\text{V}, I_C=50\text{mA}$	30		
f_T	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	100	300	MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$		6.0	pF
h_{fe}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	50	200	
NF	$V_{CE}=5.0\text{V}, I_C=200\mu\text{A}, R_S=1\text{k}\Omega,$ $f=10\text{Hz to } 15.7\text{kHz}$		8.0	dB

CMLT5551

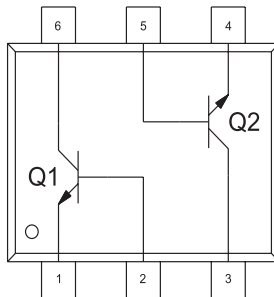
**SURFACE MOUNT SILICON
DUAL, HIGH VOLTAGE
NPN TRANSISTOR**



SOT-563 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



LEAD CODE:

- 1) Emitter Q1
- 2) Base Q1
- 3) Collector Q2
- 4) Emitter Q2
- 5) Base Q2
- 6) Collector Q1

MARKING CODE: 5C5

DIMENSIONS

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.0027	0.007	0.07	0.18
B	0.008		0.20	
C	0.017	0.024	0.45	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.059	0.067	1.50	1.70
G	0.043	0.051	1.10	1.30
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R2)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix " TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

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